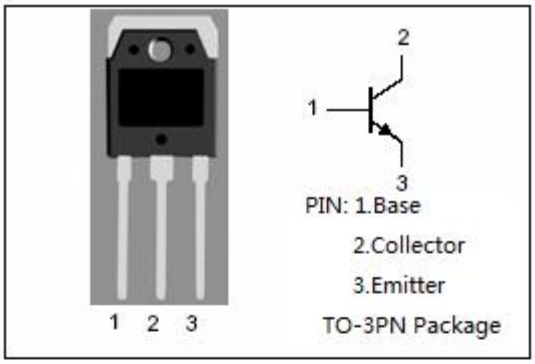
isc Silicon NPN Power Transistor — BU124



DESCRIPTION

- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$ = 150V(Min)
- High Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

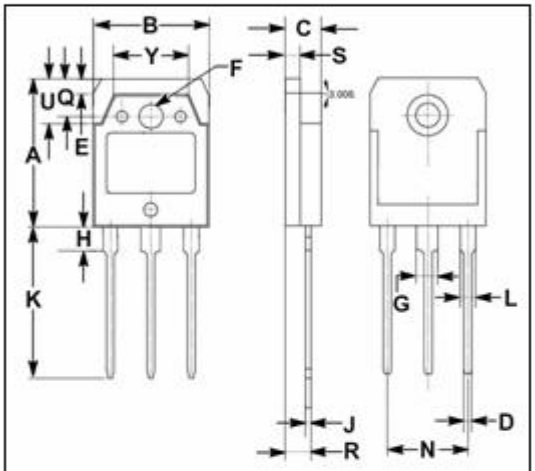
- Designed for switch-mode CTV supply systems applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	350	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	8	V
I_C	Collector Current-Continuous	10	A
I_{CM}	Collector Current-Peak	15	A
I_B	Base Current-Continuous	2	A
P_C	Collector Power Dissipation @ T_C=25℃	50	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	1.1	℃/W



DIM	mm MIN	mm MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C=50mA ;I_B= 0	150			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 4A; I_B= 0.4A			1.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 8A; I_B= 0.8A			2.0	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	I_C= 4A; I_B= 0.4A			1.5	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	I_C= 8A; I_B= 0.8A			2.5	V
I_{CBO}	Collector Base Cutoff Current	V_{CB}=350V; I_E= 0			0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 8V; I_C=0			0.1	mA
h_{FE-1}	DC Current Gain	I_C= 5A ; V_{CE}= 5V	20			
h_{FE-2}	DC Current Gain	I_C= 10A ; V_{CE}= 5V	5			
f_T	Current-Gain—Bandwidth Product	I_C= 0.5A ; V_{CE}= 10V;f_{test}= 1.0MHz	4			MHz